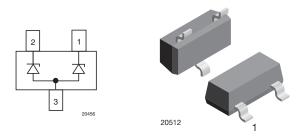
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Two-Line ESD Protection in SOT-23



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MARKING (example only)



YYY = type code (see table below) XX = date code

DESIGN SUPPORT TOOLS AVAILABLE



ls			M	00	de	ls
_	_	 _	_			

FEATURES

- Two-line ESD protection device
- ESD immunity acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



(5-2008)



ORDERIN	ORDERING INFORMATION									
	ENVIR	ONMENTAL AN	ID QUALITY CO	DDE	PACKAG	ING CODE				
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-CO LEAD (P	VIPLIANT + b)-FREE		(8 mm TAPE) (8 mm TAPE) (EX		ORDERING CODE (EXAMPLE)			
	QUALIFIED	STANDARD	GREEN	PLATED 15K/BOX = MOQ		10K/BOX = MÔQ				
GSOT05C-		E		3	-08		GSOT05C-E3-08			
GSOT05C-			G	3	-08		GSOT05C-G3-08			
GSOT05C-	н	E		3	-08		GSOT05C-HE3-08			
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08			
GSOT05C-		E		3		-18	GSOT05C-E3-18			
GSOT05C-			G	3		-18	GSOT05C-G3-18			
GSOT05C-	н	E		3		-18	GSOT05C-HE3-18			
GSOT05C-	Н		G	3		-18	GSOT05C-HG3-18			

PACKAG	PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
		C1G	Green	8.1 mg		(according J-STD-020)	max. 260 °C		
GSOT04C	SOT-23	04C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
		C8G	Green	8.1 mg		(according J-STD-020)	max. 260 °C		
GSOT05C	SOT-23	05C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
0001000	001 20	C2G	Green	8.1 mg	02 04 0 0	(according J-STD-020)	max. 260 °C		
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
6301080	301-23	C3G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
0301120	301-23	C4G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
GSUIISC	501-23	C5G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	max. 260 °C		
0007040	COT 02	24C	Standard	8.8 mg		MSL level 1	Peak temperature		
GSOT24C	SOT-23	C6G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
G30136C	301-23	C7G	Green	8.1 mg	01 94 0-0	(according J-STD-020)	max. 260 °C		

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1 For technical questions, contact: ESDprotection@vishay.com Document Number: 85824

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ABSOLUTE MAXIMU	M RATINGS GSOT03C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I	L VALUE 30 30 30 369 504 ± 30 ± 30 ± 30 -55 to +150 -55 to +150	А
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}		А
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	Р	369	W
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	504	W
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30 30 369 504 ± 30 ± 30 -55 to +150	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	С°

ABSOLUTE MAXIMUM RATINGS GSOT04C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Dealers have small	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μ s; single shot		30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	30	А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μ s; single shot	P _{PP}	429	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	ГРР	564	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30 30 429 564	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT05C							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		30	А			
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	Іррм		А			
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	480	W			
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	грр	612	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-55 to +150	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

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ABSOLUTE MAXIMU	M RATINGS GSOT08C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Dook pulso ourront	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		18	А
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}		А
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	18 18 18 345 400 ± 30 ± 30 -55 to +150	W
Feak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	Грр		W
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	18 18 345 400 ± 30 ± 30 -55 to +150	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{STG}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS GSOT12C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Data la sura	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		12	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM		А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	312	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	ГРР	337	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD minuting	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	12 312 337 ± 30 ± 30 -55 to +150	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT15C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot		8	А		
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM	8 8 345 400 ± 30 ± 30 -55 to +150	А		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	Р	345	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	400	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

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ABSOLUTE MAXIMUM RATINGS GSOT24C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I	5	А		
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	IPPM		А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	235	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	грр	240	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	5 5 235 240 ± 30 ± 30 -55 to +150	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT36C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Ded to be a south	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot		3.5	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	IPPM		А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	P _{PP}	3.5 248 252 ± 30 ± 30	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \ \mu$ s; single shot	грр		W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD minumity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		





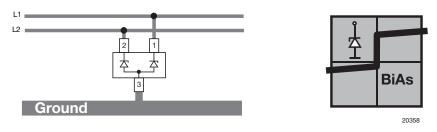
BIAs-MODE (2-line Bidirectional Asymmetrical protection mode)

With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V_{RWM}) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

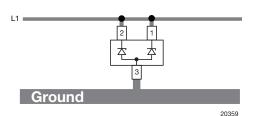
Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).



If a higher surge current or peak pulse current (I_{PP}) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

This offers:

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C_D)
- double reverse leakage current (2 x I_R)



ELECTRICAL CHARACTERISTICS GSOT03C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	3.3	V		
Reverse voltage	at I _R = 100 μA	V _R	3.3	-	-	V		
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4.0	4.6	5.5	V		
	at I _{PP} = 1 A	V	-	5.7	7.5	V		
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	10	MAX. 2 3.3 - 100 5.5	V		
Forward alamaing valtage	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _F	-	4.5	-	V		
Canacitanaa	at V _R = 0 V; f = 1 MHz	0	-	420	600	pF		
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF		

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ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	4	V			
Reverse voltage	at I _R = 20 μA	V _R	4	-	-	V			
Reverse current	at V _R = 4 V	I _R	-	-	20	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5	6.1	7	V			
	at I _{PP} = 1 A	V	-	7.5	9	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	11.2	14.3	V			
	at I _{PP} = 1 A	N	-	1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V			
Canaditanaa	at $V_R = 0 V$; f = 1 MHz	C _D	-	310	450	pF			
Capacitance	at V _R = 2 V; f = 1 MHz		-	200	-	pF			

ELECTRICAL CHARACTERISTICS GSOT05C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V
Reverse voltage	at I _R = 10 μA	V _R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	10	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6	6.8	8	V
	at I _{PP} = 1 A	V	-	7	8.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	12	16	V
Forward clamping valtage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Canaaitanaa	at $V_R = 0 V$; f = 1 MHz	0	-	260	60 350	pF
Capacitance	at V _R = 2.5 V; f = 1 MHz	C _D	-	150	-	pF

between pin 1 to pin 3 or	pin 2 to pin 3					
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	8	V
Reverse voltage	at I _R = 5 μA	V _R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9	10	11	V
Deverse elemening voltage	at I _{PP} = 1 A	V	-	10.7	13	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _C	-	15.2	19.2	V
Ferward elemening valtage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V
O	at $V_R = 0 V$; f = 1 MHz	•	-	160	250	pF
Capacitance	at V _B = 4 V; f = 1 MHz	CD	-	80	-	pF

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ELECTRICAL CHARAC between pin 1 to pin 3 or	TERISTICS GSOT12C (T _{amb} = 25 pin 2 to pin 3	°C unless (otherwise	specified)	
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V
Reverse voltage	at I _R = 1 μA	V _R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15	16.5	V
	at I _{PP} = 1 A	V	-	15.4	18.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V
Forward elemains voltage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V
Conceitonee	at $V_R = 0 V$; f = 1 MHz	CD	-	115	150	pF
Capacitance	at V _R = 6 V; f = 1 MHz		-	50	-	pF

ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	15	V			
Reverse voltage	at I _R = 1 μA	V _R	15	-	-	V			
Reverse current	at V _R = 15 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	16.5	18	20	V			
	at I _{PP} = 1 A	V	-	19.4	23.5	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _C	-	24.8	28.8	V			
Forward elemening veltage	at I _{PP} = 1 A	N	-	1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _F	-	1.8	-	V			
Canacitanaa	at $V_R = 0$ V; f = 1 MHz		-	90	120	pF			
Capacitance	at V _R = 7.5 V; f = 1 MHz	C _D	-	35	-	pF			

ELECTRICAL CHARAC	TERISTICS GSOT24C (T _{amb} = 25 pin 2 to pin 3	°C unless	otherwise	specified)	
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V
Reverse current	at V _R = 24 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27	30	33	V
	at I _{PP} = 1 A	N	-	34	41	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V
E	at I _{PP} = 1 A	N	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V
0	at V _R = 0 V; f = 1 MHz	_	-	65	80	pF
Capacitance	at V _B = 12 V; f = 1 MHz	CD	-	20	-	pF

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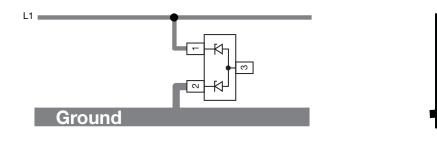
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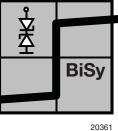
ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	36	V			
Reverse voltage	at I _R = 1 μA	V _R	36	-	-	V			
Reverse current	at V _R = 36 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39	43	47	V			
	at I _{PP} = 1 A	V	-	49	60	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _C	-	59	71	V			
	at I _{PP} = 1 A	V	-	1	1.2	V			
Forward clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _F	-	1.3	-	V			
Consoltance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	52	65	pF			
Capacitance	at V _R = 18 V; f = 1 MHz		-	12	-	pF			

BiSy-MODE (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





ELECTRICAL CHARACTERISTICS GSOT03C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected **TEST CONDITIONS/REMARKS** SYMBOL MIN. UNIT PARAMETER TYP. MAX. Protection paths Number of lines which can be protected -1 lines N_{channel} _ V Reverse stand-off voltage Max. reverse working voltage 3.8 V_{RWM} _ _ Reverse voltage at $I_{\rm R} = 100 \ \mu A$ V_R 3.8 _ V at $V_{\rm R} = 3.8$ V 100 Reverse current I_R -μA Reverse breakdown voltage at $I_{R} = 1 \text{ mA}$ 4.5 5.3 6.2 ۷ V_{BR} V at $I_{PP} = 1 A$ -7 8.4 Reverse clamping voltage V_{C} 16.8 V at $I_{PP} = I_{PPM} = 30 \text{ A}$ 14 _ at $V_B = 0 V$; f = 1 MHz 210 300 рF _ Capacitance CD at $V_{B} = 1.6 V$; f = 1 MHz 190 _ pF

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	ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT				
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines				
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	4.5	V				
Reverse voltage	at I _R = 20 μA	V _R	4.5	-	-	V				
Reverse current	at V _R = 4.5 V	I _R	-	-	20	μΑ				
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5.5	6.8	7.7	V				
Deverse elements veltage	at I _{PP} = 1 A	M	-	7.5	9	V				
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	15.7	18.8	V				
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	155	225	pF				
	at $V_R = 2 V$; f = 1 MHz		-	135	-	pF				

ELECTRICAL CHARACTERISTICS GSOT05C ($T_{amb} = 25$ °C unless otherwise specified)

between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5.5	V			
Reverse voltage	at I _R = 10 μA	V _R	5.5	-	-	V			
Reverse current	at V _R = 5.5 V	I _R	-	-	10	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6.5	7.5	8.7	V			
Poweree elemping veltage	at I _{PP} = 1 A	V	-	8.1	9.7	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	17	20.4	V			
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	130	175	pF			
	at $V_R = 4 V$; f = 1 MHz		-	100	-	pF			

ELECTRICAL CHARACTERISTICS GSOT08C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	8.5	V
Reverse voltage	at I _R = 5 μA	V _R	8.5	-	-	V
Reverse current	at V _R = 8.5 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9.5	10.7	11.7	V
Poverse elemping veltage	at I _{PP} = 1 A	V	-	11.7	14	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 18 \text{ A}$	V _C	-	18.5	22.2	V
Canacitanaa	at $V_R = 0 V$; f = 1 MHz	6	-	80	125	pF
Capacitance	at $V_R = 4 V$; f = 1 MHz	C _D	-	60	-	pF

ELECTRICAL CHARACTERISTICS GSOT12C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12.5	V
Reverse voltage	at I _R = 1 μA	V _R	12.5	-	-	V
Reverse current	at V _R = 12.5 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15.7	16.5	V
Powerse elemping veltage	at I _{PP} = 1 A	V	-	16.4	19.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	_A = 12 A V _C -	-	23.4	28.1	V
Capacitanaa	at $V_R = 0 V$; f = 1 MHz	CD	-	58	75	pF
Capacitance	at V _R = 7.5 V; f = 1 MHz		-	36	-	pF

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	ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT				
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines				
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	15.5	V				
Reverse voltage	at I _R = 1 μA	V _R	15.5	-	-	V				
Reverse current	at V _R = 15.5 V	I _R	-	-	1	μA				
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	17	18.7	20.7	V				
Bowerse elemping veltage	at I _{PP} = 1 A	V	-	20.4	24.5	V				
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 8 A$	V _C	-	26.6	30.6	V				
Capacitance	at $V_R = 0 V$; f = 1 MHz	C _D	-	45	60	pF				
	at V _R = 7.5 V; f = 1 MHz		-	25	-	pF				

ELECTRICAL CHARACTERISTICS GSOT24C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24.5	V		
Reverse voltage	at I _R = 1 μA	V _R	24.5	-	-	V		
Reverse current	at V _R = 24.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27.5	30.7	33.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	34	41	V		
	at $I_{PP} = I_{PPM} = 5 A$		-	40	48	V		
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	33	40	pF		
	at V _R = 12 V; f = 1 MHz		-	18	-	pF		

ELECTRICAL CHARACTERISTICS GSOT36C ($T_{amb} = 25$ °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

between pin 1 to pin 2 to pin 2 to pin 6 hot connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	Nchannel	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	36.5	V			
Reverse voltage	at I _R = 1 μA	V _R	36.5	-	-	V			
Reverse current	at V _R = 36.5 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39.5	43.7	47.7	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	50	60	V			
	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$		-	60	72	V			
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	26	33	pF			
	at V _R = 18 V; f = 1 MHz		-	10	-	pF			



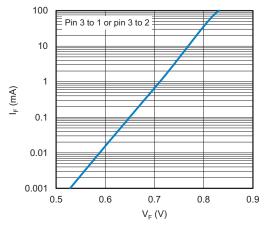


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

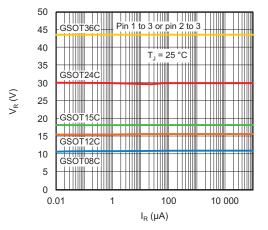


Fig. 2 - Typical Reverse Voltage V_R vs. Reverse Current I_R

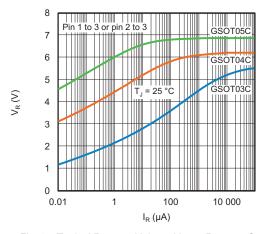


Fig. 3 - Typical Reverse Voltage V_R vs. Reverse Current I_R

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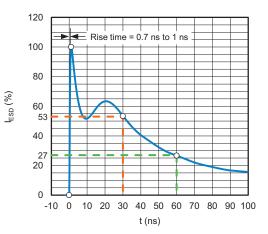


Fig. 4 - ESD Discharge Current Waveform According to IEC 61000-4-2 (330 Ω / 150 pF)

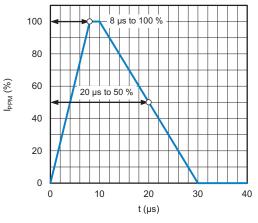


Fig. 5 - 8/20 µs Peak Pulse Current Waveform According to IEC 61000-4-5

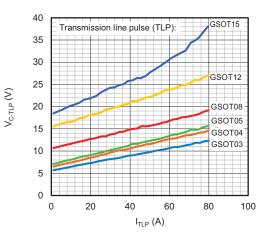


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

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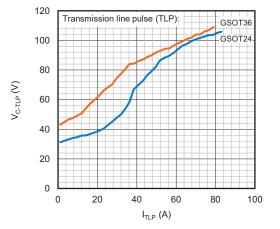


Fig. 7 - Typical Clamping Voltage vs. Peak Pulse Current

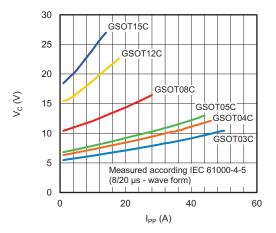


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

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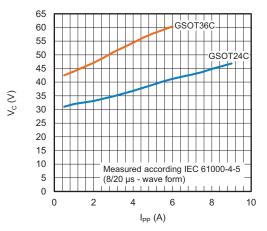


Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

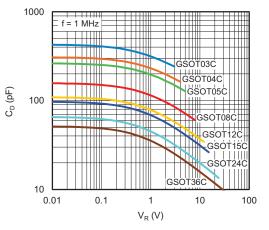


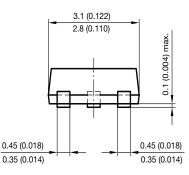
Fig. 10 - Typical Capacitance vs. Reverse Voltage

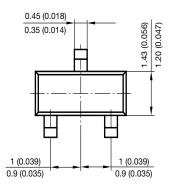
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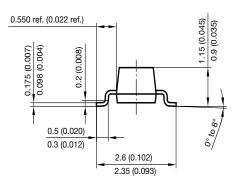


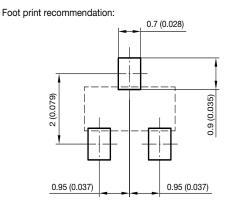
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PACKAGE DIMENSIONS in millimeters (inches): SOT-23

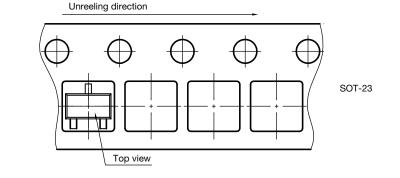








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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607

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